

## QIAOXIN N-Channel **Super Trench II** Power MOSFET

### Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(on)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

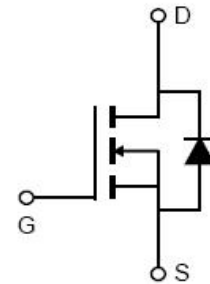
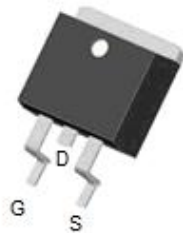
### General Features

- $V_{DS} = 85V, I_D = 200A$   
 $R_{DS(on)} = 2.55m\Omega$ , typical (TO-220) @  $V_{GS} = 10V$   
 $R_{DS(on)} = 2.4m\Omega$ , typical (TO-263) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

**TO-220**



**TO-263**



**Schematic Diagram**

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VCRRP028N85	VCRRP028N85	TO-220	-	-	-
VCRRP028N85D	VCRRP028N85D	TO-263	-	-	-

### Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	85	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	200	A
Drain Current-Continuous ( $T_c = 100^\circ C$ )	$I_D(100^\circ C)$	150	A
Pulsed Drain Current	$I_{DM}$	800	A
Maximum Power Dissipation	$P_D$	245	W
Derating factor		1.63	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 1)</sup>	$E_{AS}$	1767	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.61	$^{\circ}C/W$
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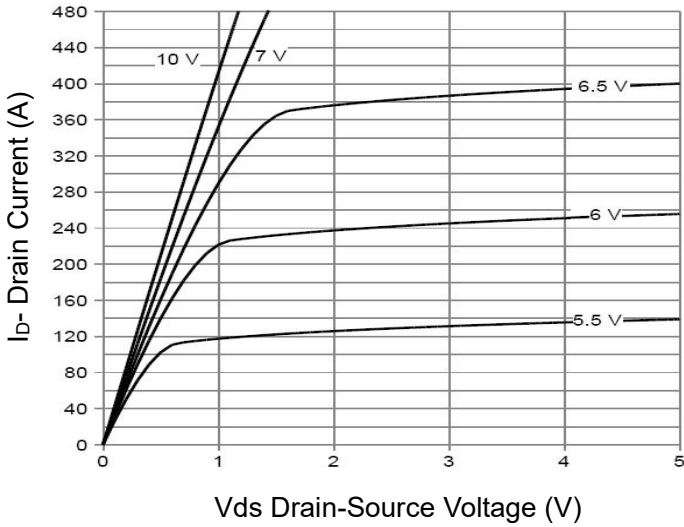
## Electrical Characteristics ( $T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
<b>Off Characteristics</b>							
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	85		-	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=85V, V_{GS}=0V$	-	-	1	$\mu A$	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA	
<b>On Characteristics</b>							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=100A$	TO-220	-	2.55	2.8	m $\Omega$
			TO-263		2.4	2.8	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=100A$		200	-	S	
<b>Dynamic Characteristics</b>							
Input Capacitance	$C_{iss}$	$V_{DS}=40V, V_{GS}=0V,$ $F=1.0MHz$	-	7680	-	PF	
Output Capacitance	$C_{oss}$		-	1472	-	PF	
Reverse Transfer Capacitance	$C_{rss}$		-	60	-	PF	
<b>Switching Characteristics</b> (Note 2)							
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=40V, I_D=100A$ $V_{GS}=10V, R_G=1.6\Omega$	-	25	-	nS	
Turn-on Rise Time	$t_r$		-	15	-	nS	
Turn-Off Delay Time	$t_{d(off)}$		-	52	-	nS	
Turn-Off Fall Time	$t_f$		-	17	-	nS	
Total Gate Charge	$Q_g$	$V_{DS}=40V, I_D=100A,$ $V_{GS}=10V$	-	124	-	nC	
Gate-Source Charge	$Q_{gs}$		-	37		nC	
Gate-Drain Charge	$Q_{gd}$		-	33		nC	
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=100A$	-		1.2	V	
Diode Forward Current	$I_S$		-	-	200	A	
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = 100A$ $di/dt = 100A/\mu s$	-	98	-	nS	
Reverse Recovery Charge	$Q_{rr}$		-	280	-	nC	

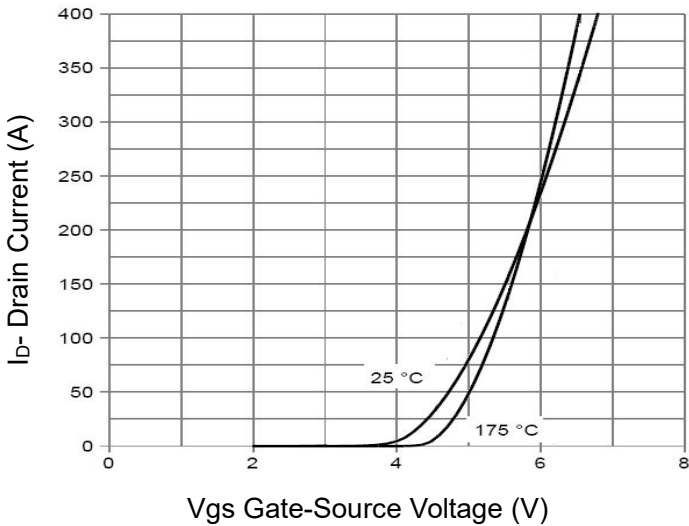
### Notes:

1. EAS condition :  $T_J=25^{\circ}C, V_{DD}=40V, V_G=10V, L=0.5mH, R_G=25\Omega$
2. Guaranteed by design, not subject to production.
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink k, assuming a maximum junction temperature of  $T_J(MAX)=175^{\circ}C$ . The SOA curve provides a single pulse rating.

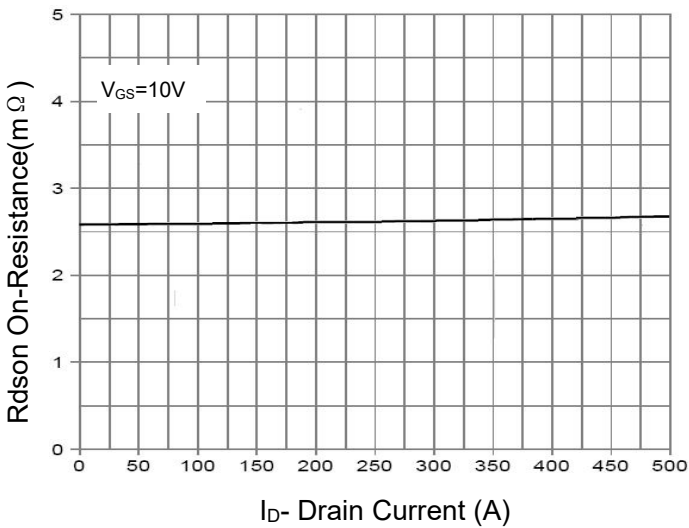
**Typical Electrical and Thermal Characteristics**



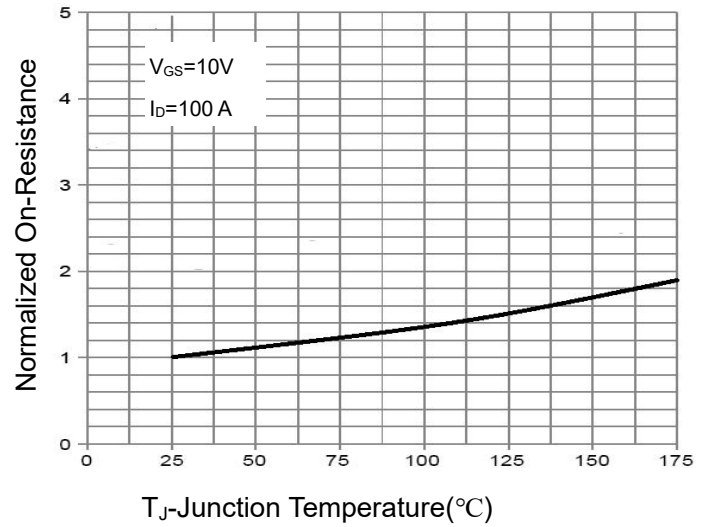
**Figure 1 Output Characteristics**



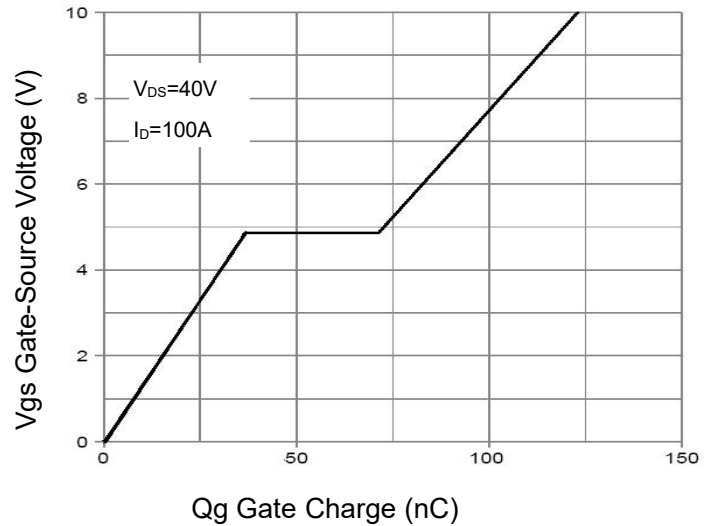
**Figure 2 Transfer Characteristics**



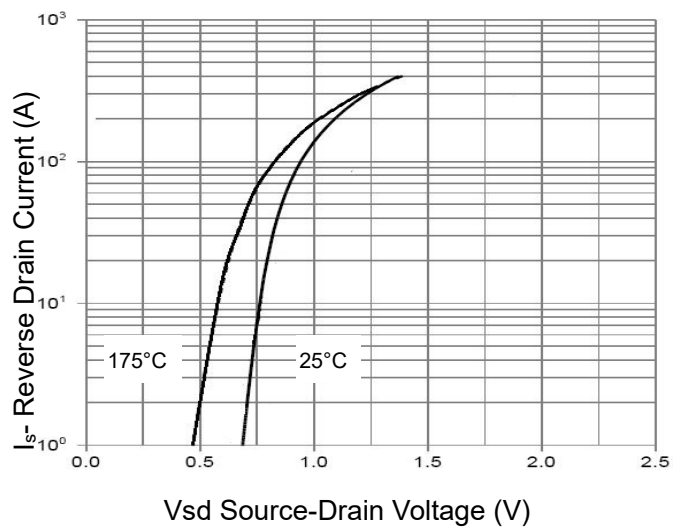
**Figure 3 Rdson- Drain Current**



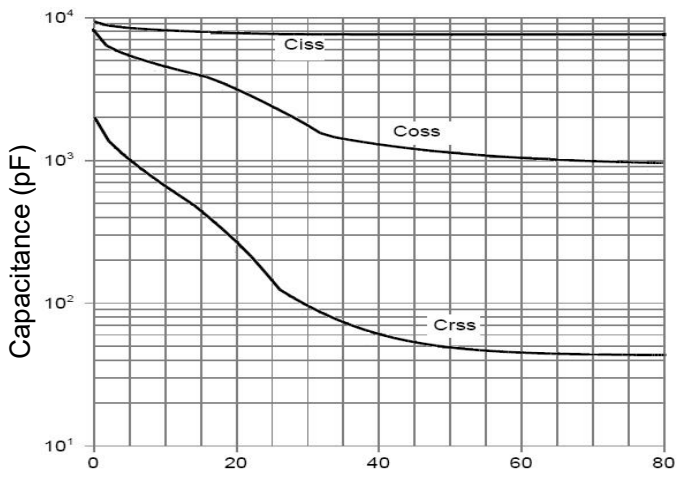
**Figure 4 Rdson-Junction Temperature**



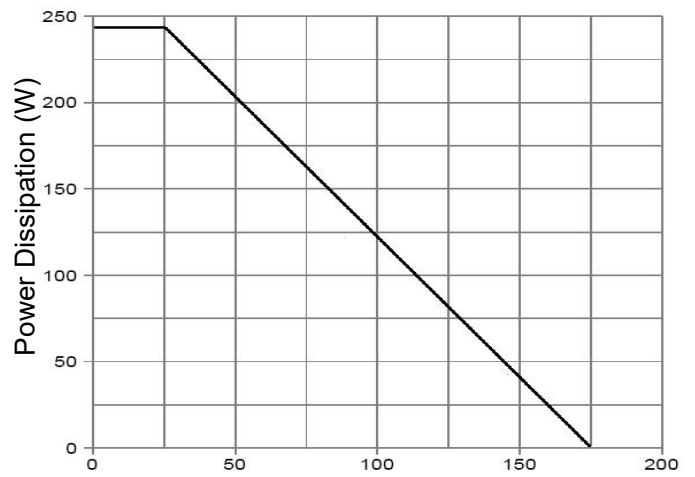
**Figure 5 Gate Charge**



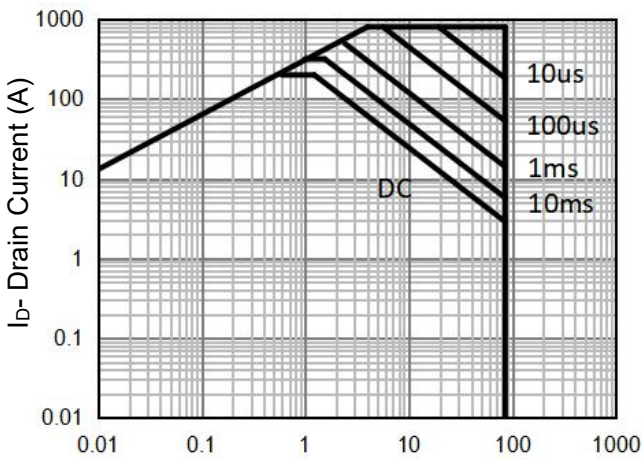
**Figure 6 Source- Drain Diode Forward**



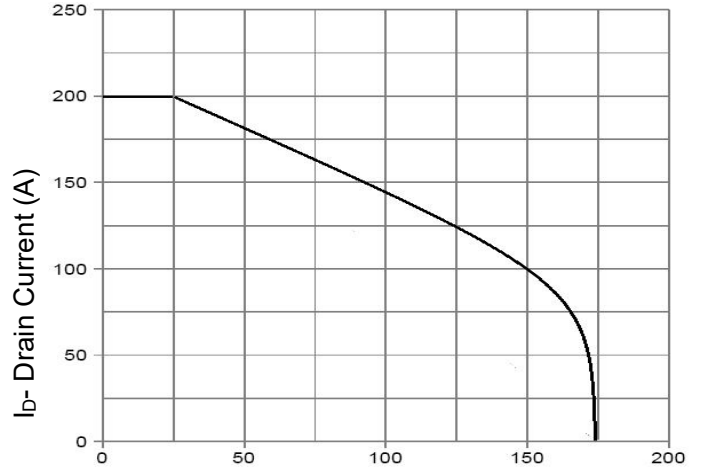
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



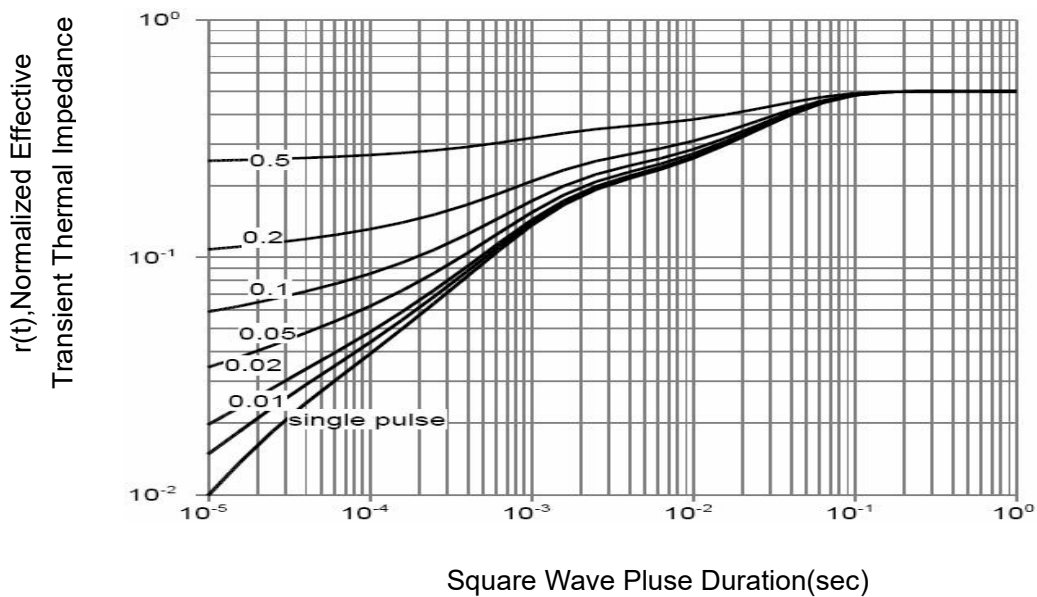
TA-Junction Temperature(°C)  
**Figure 9 Power De-rating**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area** (Note 3)

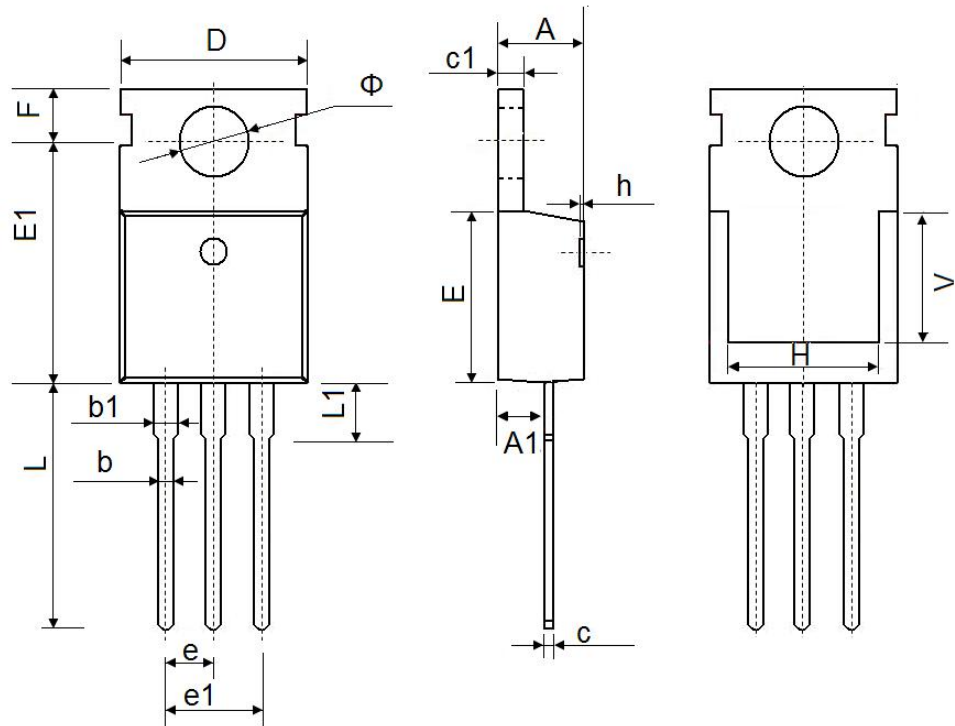


TA-Junction Temperature (°C)  
**Figure 10 Current De-rating**



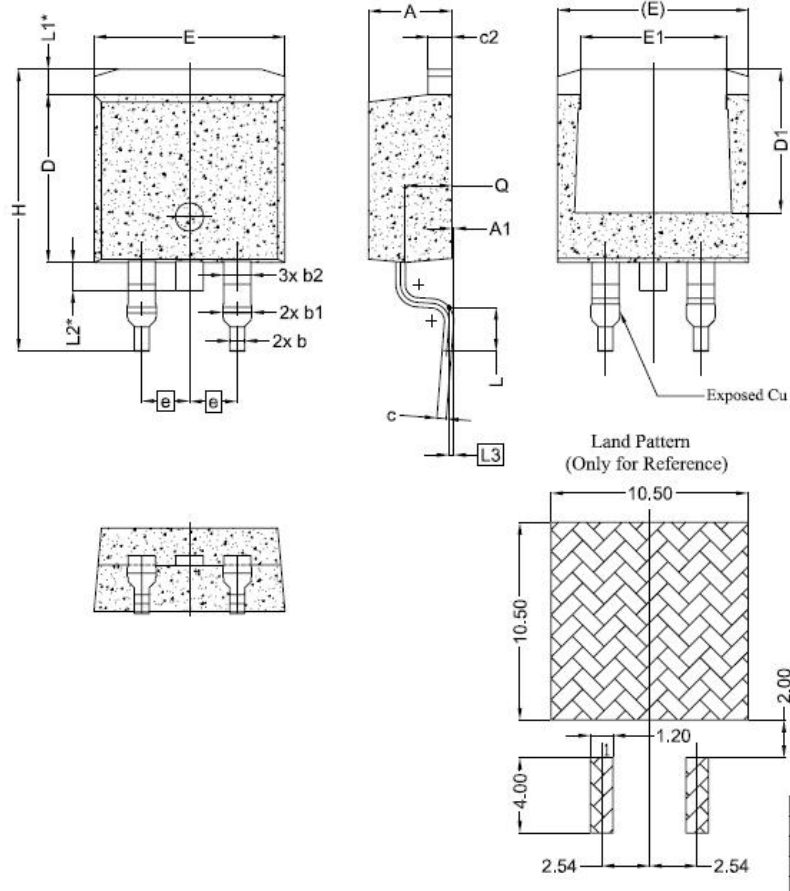
Square Wave Pluse Duration(sec)  
**Figure 11 Normalized Maximum Transient Thermal Impedance**

**TO-220-3L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150

**TO-263-2L Package Information**



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70



### **Attention**

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